Diode Semiconductor Device - Page 1 of 1



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Inclosure Material: Glass Overall Length: 0.350 inches Terminal Length: 1.250 inches Overall Diameter: 0.255 inches Overall Diameter: 0.255 inches Function For Which Designed: Transient suppressor Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-13 Mounting Method: Terminal Features Provided: Hermetically sealed case Semiconductor Material: Silicon Voltage Rating In Volts Per Characteristic: 10.0 reverse voltage, dc and 12.6 breakdown voltage, dc Current Rating Per Characteristic: 1.00 milliamperes forward current, total rms nanoamperes Power Rating Per Characteristic: 1500.0 watts small-signal input power, common-emitter megahertz Maximum Operating Tempurature Per Measurement Point: 175.0 degrees celsius ambient air
Overall Length:         0.350 inches         Terminal Length:         1.250 inches         Overall Diameter:         0.225 inches         Function For Which Designed:         Transient suppressor         Joint Electronic Device Engineering Council/jedec/case Outline Designation:         Do-13         Mounting Method:         Terminal         Features Provided:         Hermetically sealed case         Semiconductor Material:         Silicon         Voltage Rating In Volts Per Characteristic:         1.00 reverse voltage, dc and 12.6 breakdown voltage, dc         Current Rating Per Characteristic:         1.00 milliamperes forward current, total rms nanoamperes         Power Rating Per Characteristic:         1.00 watts small-signal input power, common-emitter megahertz         Maximum Operating Tempurature Per Measurement Point:
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Terminal Length:         1.250 inches         Overall Diameter:         0.225 inches         Function For Which Designed:         Transient suppressor         Joint Electronic Device Engineering Council/jedec/case Outline Designation:         Do-13         Mounting Method:         Terminal         Features Provided:         Hermetically sealed case         Semiconductor Material:         Silicon         Voltage Rating In Volts Per Characteristic:         10.0 reverse voltage, dc and 12.6 breakdown voltage, dc         Current Rating Per Characteristic:         1.00 milliamperes forward current, total rms nanoamperes         Power Rating Per Characteristic:         1500.0 watts small-signal input power, common-emitter megahertz         Maximum Operating Tempurature Per Measurement Point:
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1500.0 watts small-signal input power, common-emitter megahertz Maximum Operating Tempurature Per Measurement Point:
Maximum Operating Tempurature Per Measurement Point:
Terminal Type And Quantity:
2 uninsulated wire lead
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig:
A110a0